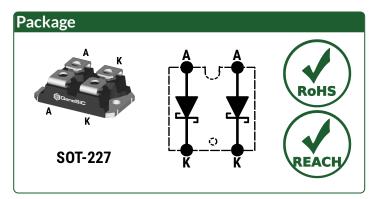
GeneSic

Silicon Carbide Schottky Diode

 V_{RRM} = 1700 V $I_{F(T_C = 145 \circ C)}$ = 50 A * Q_C = 412 nC *

Features

- Gen4 Thin Chip Technology for Low V_F
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Qc/IF
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V_F
- Low V_F for High Temperature Operation



Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Improved System Efficiency

Applications

- EV Fast Chargers
- Solar Inverters
- Wind Energy Converters
- Train Auxiliary Power Supplies
- High Frequency Rectifiers
- Switched Modé Power Supplies
- Motor Drives
- Pulsed Power

Absolute Maximum Ratings (At T _C = 25°C Unless Otherwise Stated)										
Parameter	Symbol	Conditions Values		Unit	Note					
Repetitive Peak Reverse Voltage (Per Leg)	V_{RRM}		1700	٧						
Continuous Forward Current (Per Leg / Per Device)	IF	$T_C = 75^{\circ}C$, D = 1	50 / 100							
		$T_C = 100^{\circ}C, D = 1$	43 / 86	Α	Fig. 4					
		$T_C = 145^{\circ}C, D = 1$	25 / 50							
Non-Repetitive Peak Forward Surge Current, Half Sine Wave (Per Leg)	I _{F,SM}	T_C = 25°C, t_P = 10 ms	250	Α						
		T_C = 150°C, t_P = 10 ms	200							
Repetitive Peak Forward Surge Current, Half Sine Wave	I _{F,RM}	T_C = 25°C, t_P = 10 ms	150	Α						
(Per Leg)		T_C = 150°C, t_P = 10 ms	105	A						
Non-Repetitive Peak Forward Surge Current (Per Leg)	I _{F,MAX}	T_C = 25°C, t_P = 10 μ s	1250	Α						
i ² t Value (Per Leg)	∫i²dt	T_C = 25°C, t_P = 10 ms	312	A ² s						
Non-Repetitive Avalanche Energy (Per Leg)	E _{AS}	$L = 1.6 \text{ mH}, I_{AS} = 25 \text{ A}$	500	mJ						
Diode Ruggedness (Per Leg)	dV/dt	V _R = 0 ~ 1360 V	200	V/ns						
Power Dissipation (Per Leg / Per Device)	P _{TOT}	T _C = 25°C	262 / 524	W	Fig. 3					
Operating and Storage Temperature	T _j , T _{stg}		-55 to 175	°C						

^{*} Per Device

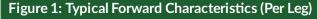




Electrical Characteristics (Per Leg) Values **Parameter Symbol Conditions** Unit Note Min. Тур. Max. $I_F = 25 A$, $T_i = 25$ °C 1.5 1.8 ٧ Diode Forward Voltage V_{F} Fig. 1 $I_F = 25 \text{ A}, T_j = 175^{\circ}\text{C}$ 2.1 $V_R = 1700 \text{ V, } T_i = 25^{\circ}\text{C}$ 1 20 **Reverse Current** Fig. 2 I_R μΑ $V_R = 1700 \text{ V}, T_j = 175^{\circ}\text{C}$ 16 $V_R = 600 V$ 141 **Total Capacitive Charge** $Q_{\mathbb{C}}$ nC Fig. 7 $V_R = 1200 V$ 206 $I_F \leq I_{F,MAX}$ $dI_F/dt = 200 A/\mu s$ $V_R = 600 V$ Switching Time < 10 ts ns $V_R = 1200 V$ $V_R = 1 V$, f = 1MHz1803 С **Total Capacitance** рF Fig. 6 V_R = 1200 V, f = 1MHz 99

Thermal/Package Characteristics										
Parameter	Symbol	Conditions	Values			Unit	Note			
			Min.	Тур.	Max.	Ullit	Note			
Thermal Resistance, Junction - Case (Per Leg)	R _{thJC}			0.57		°C/W	Fig. 9			
Weight	W _T			28.0		g				
Mounting Torque	T _M	Screws to Heatsink			1.5	Nm				
Terminal Connection Torque	Tc	M4 Screws			1.3	Nm				
Isolation Voltage(RMS)	V _{ISO}	t = 1s (50/60 Hz)		3000		V				
		t = 60s (50/60 Hz)		2500		V				
Creepage Distance on Surface	d _{Ctt}	Terminal to Terminal		10.5		mm				
	d _{Ctb}	Terminal to Backside		8.5		mm				
Striking Distance Through Air	d _{Stt}	Terminal to Terminal		3.2		mm				
	d_{Stb}	Terminal to Backside		6.8		mm				





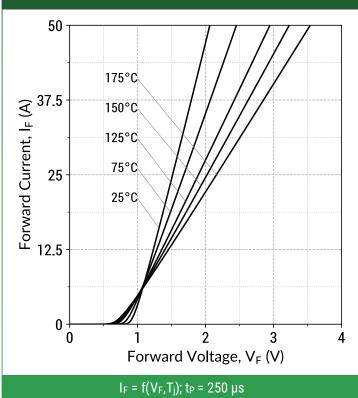


Figure 2: Typical Reverse Characteristics (Per Leg)

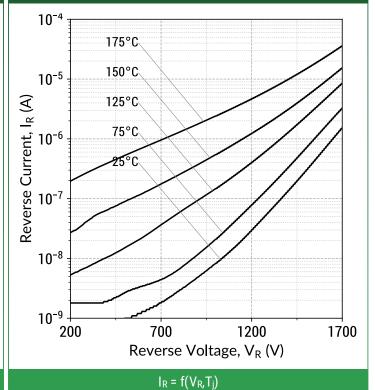


Figure 3: Power Derating Curves (Per Leg)

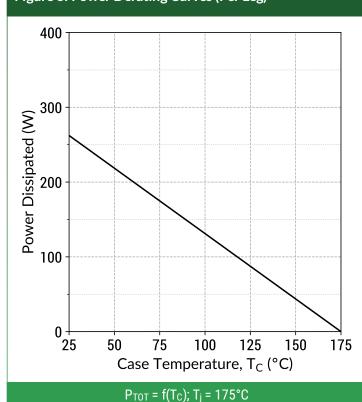


Figure 4: Current Derating Curves (Typical V_F) (Per Leg)

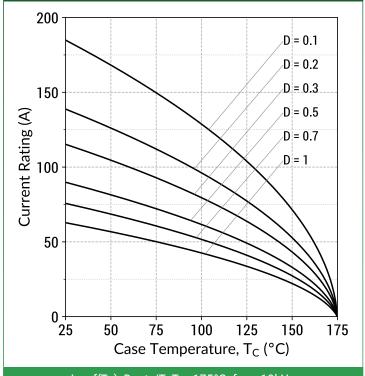
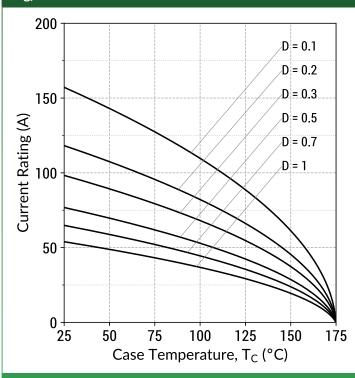


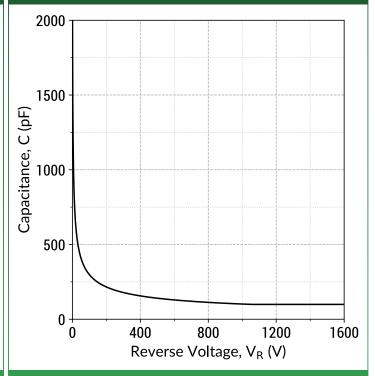


Figure 5: Current Derating Curves (Maximum V_F) (Per Leg)



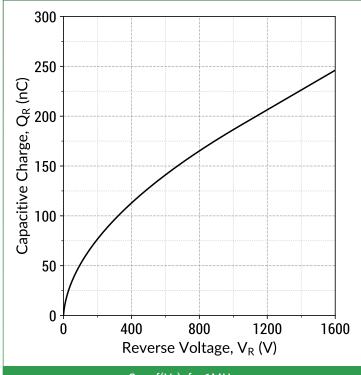
 $I_F = f(T_C); D = t_P/T; T_j \le 175$ °C; $f_{SW} > 10$ kHz

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics (Per Leg)



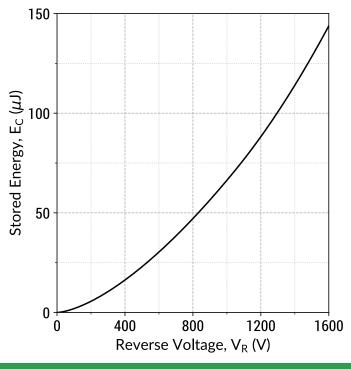
 $C = f(V_R)$; f = 1MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics (Per Leg)



 $Q_C = f(V_R); f = 1MHz$

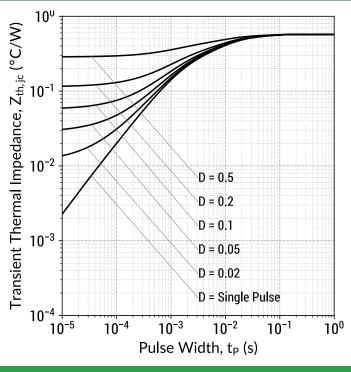
Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics (Per Leg)



 $E_C = f(V_R)$; f = 1MHz

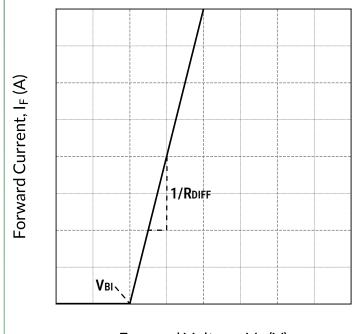


Figure 9: Transient Thermal Impedance (Per Leg)



 $Z_{th,jc} = f(t_P,D); D = t_P/T$

Figure 10: Forward Curve Model (Per Leg)



Forward Voltage, $V_F(V)$

 $I_F = f(V_F, T_j)$

Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF} (A)$

Built-In Voltage (V_{BI}):

 $V_{BI}(T_j) = m \times T_j + n (V)$ $m = -0.00126 (V/^{\circ}C)$ n = 0.997 (V)

Differential Resistance (RDIFF):

 $R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$ $a = 4.08e-07 (\Omega/^{\circ}C^2)$ $b = 0.000141 (\Omega/^{\circ}C)$ $c = 0.0182 (\Omega)$

Forward Power Loss Equation:

 $P_{LOSS} = V_{BI}(T_i) \times I_{AVG} + R_{DIFF}(T_i) \times I_{RMS}^2$



Package Dimensions SOT-227 Package Outline 0.472 (11.9) 0.480 (12.19) 1.240 (31.5) 1.255 (31.88) 0.372 (9.45) 0.378 (9.60) 0.310 (7.87) 0.322 (8.18) 0.108 (2.74) 0.124 (3.15) Ø <u>0.163 (4.14)</u> 0.169 (4.29) R 3.97 0.990 (25.1) 1.000 (25.40) 0.495 (12.5) 0.506 (12.85) 0.172 (4.37) ____0.186 (4.72) 0.191 (4.85) 0.234 (5.94) 0.030 (0.76) 0.165 (4.19) 0.033 (0.84) 0.169 (4.29) 0.588 (14.9) 0.594 (15.09) 1.186 (30.1) 1.192 (30.28) 1.494 (37.9) 1.504 (38.20) 1.049 (26.6) 1.059 (26.90) 0.080 (2.03) 0.084 (2.13) 0.164 (4.16) 0.174(4.42) Package View **Isolated Base**

NOTE

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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Related Links

SPICE Models: https://www.genesicsemi.com/sic-schottky-mps/GD2X25MPS17N/GD2X25MPS17N_SPICE.zip
PLECS Models: https://www.genesicsemi.com/sic-schottky-mps/GD2X25MPS17N/GD2X25MPS17N_PLECS.zip
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Reliability: https://www.genesicsemi.com/reliability
Compliance: https://www.genesicsemi.com/compliance
Quality Manual: https://www.genesicsemi.com/guality

Revision History

Rev 22/May: Initial Release



www.genesicsemi.com/sic-schottky-mps/

